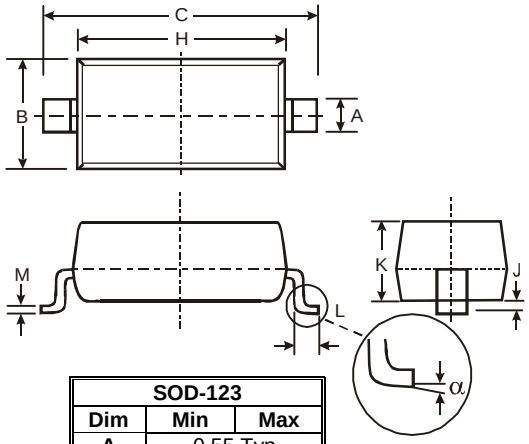
RB162M-40

1.0A Surface Mount Schottky Barrier Diode

Features

- Small power mold type.(PMDU)
- Low I_R
- High reliability



SOD-123		
Dim	**Min**	**Max**
A	0.55 Typ	
B	1.40	1.70
C	3.55	3.85
H	2.55	2.85
J	0.00	0.10
K	1.00	1.35
L	0.25	0.40
M	0.10	0.15
α	0	8°
All Dimensions in mm		

Mechanical Data

- Case: Molded Plastic

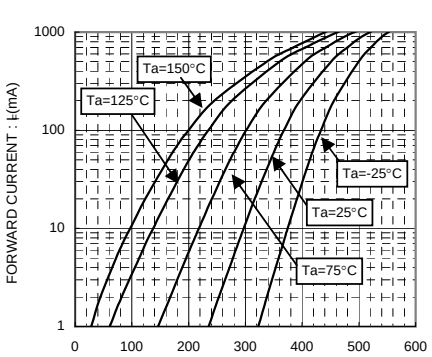
Maximum Ratings and Electrical Characteristics

@ T_A = 25°C unless otherwise specified

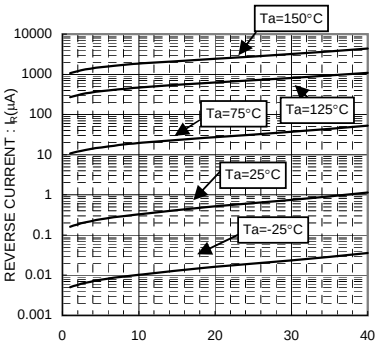
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	Io	1	A
Forward current surge peak (60Hz・1cyc)	I_{FSM}	30	A
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-40 to +150	℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.55	V	I_F=1A
Reverse current	I_R	-	-	100	μA	V_R=40V

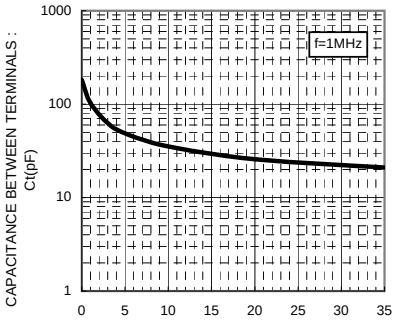
(*1)Mounting on epoxi board. (Tc=100°C MAX)



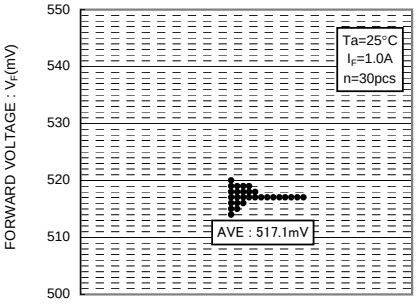
V_F-I_F CHARACTERISTICS



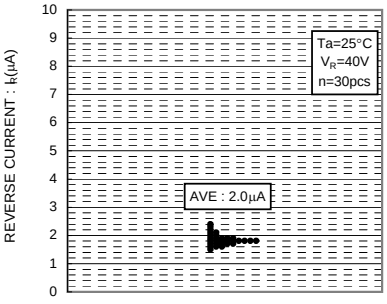
V_R-I_R CHARACTERISTICS



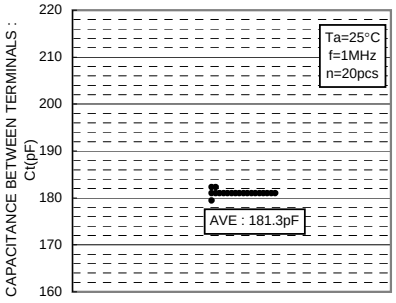
V_R-Ct CHARACTERISTICS



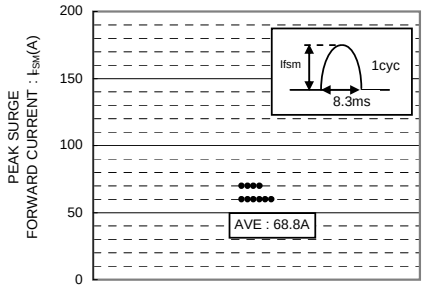
V_F DISPERSION MAP



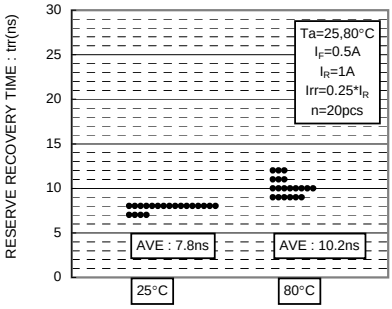
I_R DISPERSION MAP



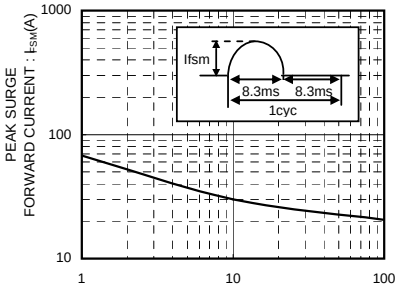
Ct DISPERSION MAP



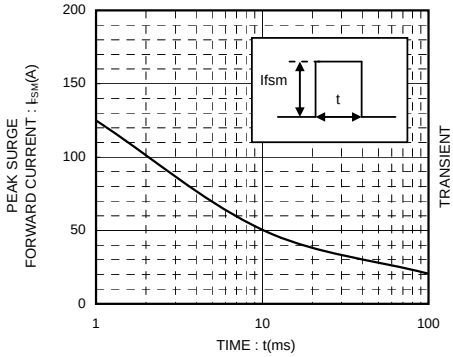
I_{FSM} DISPERSION MAP



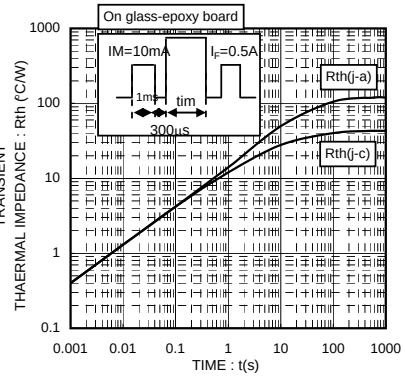
trr DISPERSION MAP



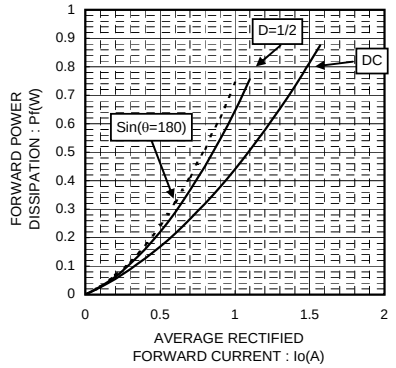
I_{FSM}-CYCLE CHARACTERISTICS



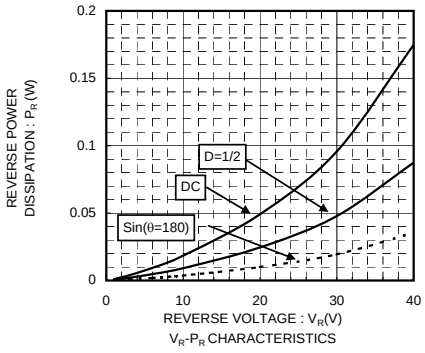
I_{FSM}-t CHARACTERISTICS



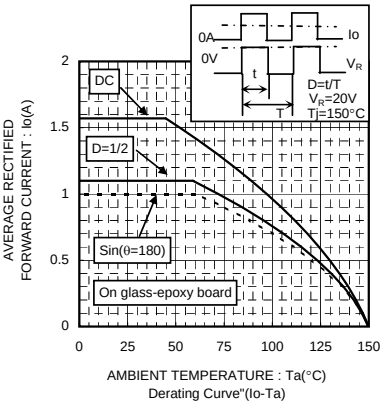
Rth-t CHARACTERISTICS



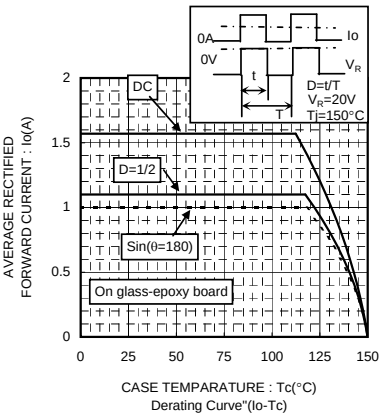
Io-Pf CHARACTERISTICS



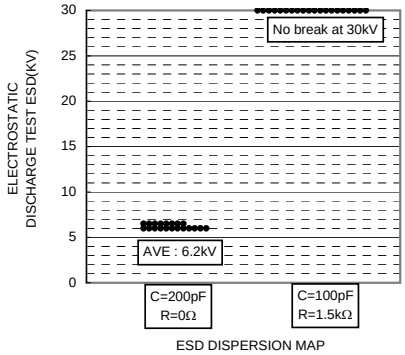
V_R-P_R CHARACTERISTICS



Derating Curve"(Io-Ta)



Derating Curve"(Io-Tc)



ESD DISPERSION MAP